



Att. Docket No. 10191/1629

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Appl. Serial No. : 09/720,761 Confirmation No. 5642
Title : METHOD OF PLASMA
ETCHING OF SILICON
Applicant(s) : Franz LAERMER et al.
Filed : March 26, 2001
TC/A.U. : 1765
Examiner : Kin Chan Chen
Docket No. : 10191/1629
Customer No. : 266461

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AARON C. DEDITCH
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AMENDMENT AFTER A FINAL OFFICE ACTION

S I R:

In response to the Final Office Action mailed on June 7, 2004 (the three-month response date for which has been extended by two months from September 7, 2004 to November 7, 2004), please reconsider the above-identified application based on the following:

Amendments to the Claims are reflected in the listing of the claims which begins on page 2 of this paper.

Remarks begin on page 7 of this paper.

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